

**/ Descriptions**

SOT-89          NPN                                  Silicon NPN transistor in a SOT-89 Plastic Package.

**/ Features**

MBIT                                  -                                  ,  
KTB1124

Adoption of MBIT processes, low collector-to-emitter saturation voltage, fast Switching Speed, Large current capacity and wide ASO, Complementary to KTB1124. Halogen-free Product.

**/ Applications**

Voltage regulators ,relay drivers lamp drivers, electrical equipment.

**/ Equivalent Circuit**



PIN1 Base          PIN 2 Collector          PIN 3 Emitter

**/ Marking**

$h_{FE}$ Classifications Symbol	A	B	C
$h_{FE}$ Range	100 200	140 280	200 400
Marking	YHA	YHB	YHC

**/ Absolute Maximum Ratings(Ta=25 )**

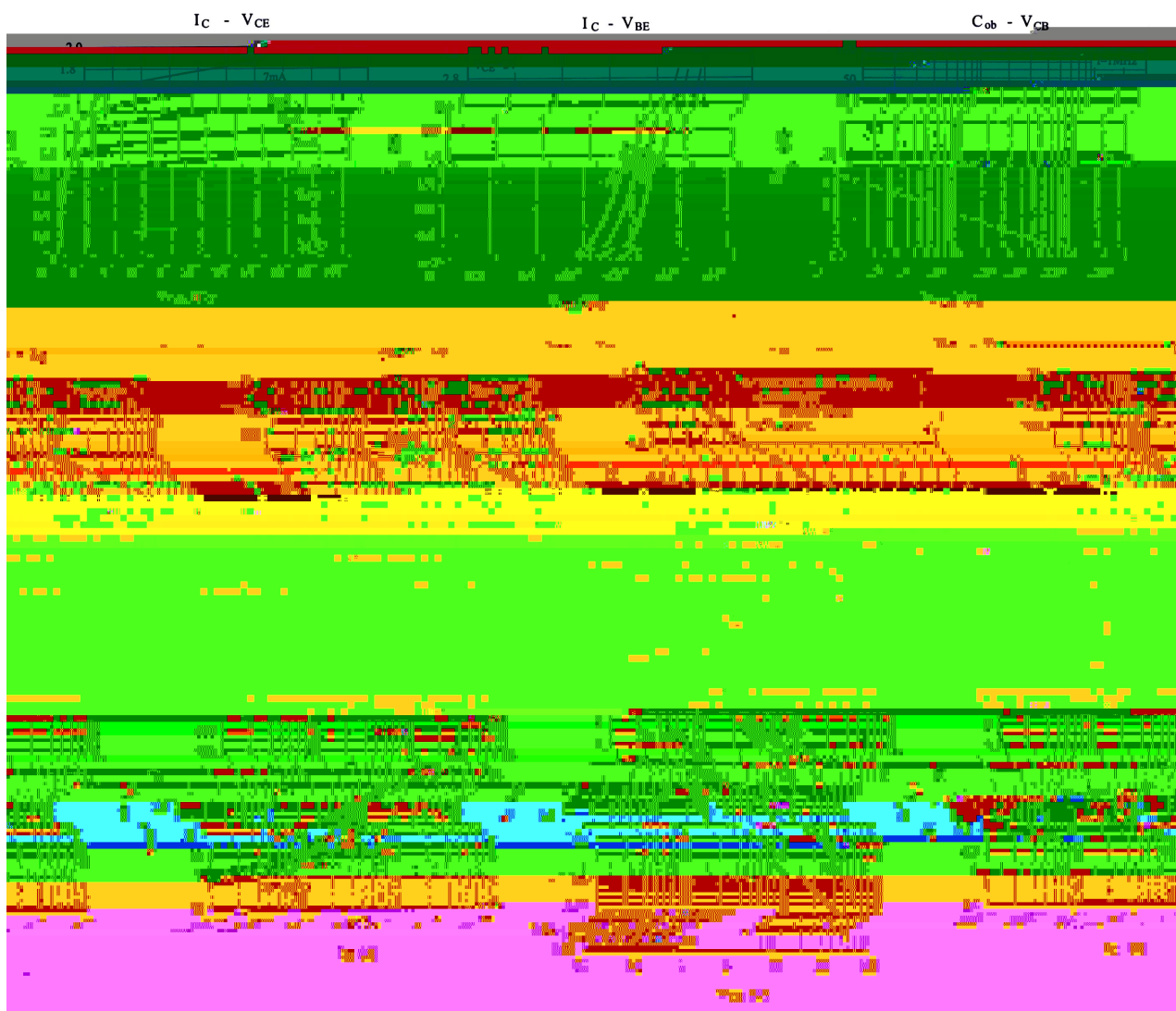
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	60	V
Collector to Emitter Voltage	$V_{CEO}$	50	V
Emitter to Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous	$I_C$	3.0	A
Collector Current – Continuous Pulse	$I_{CP}$	6.0	A
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation*	* $P_C$	1.0	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

\*:Package mounted on ceramic substrate(250mm<sup>2</sup>×0.8t)

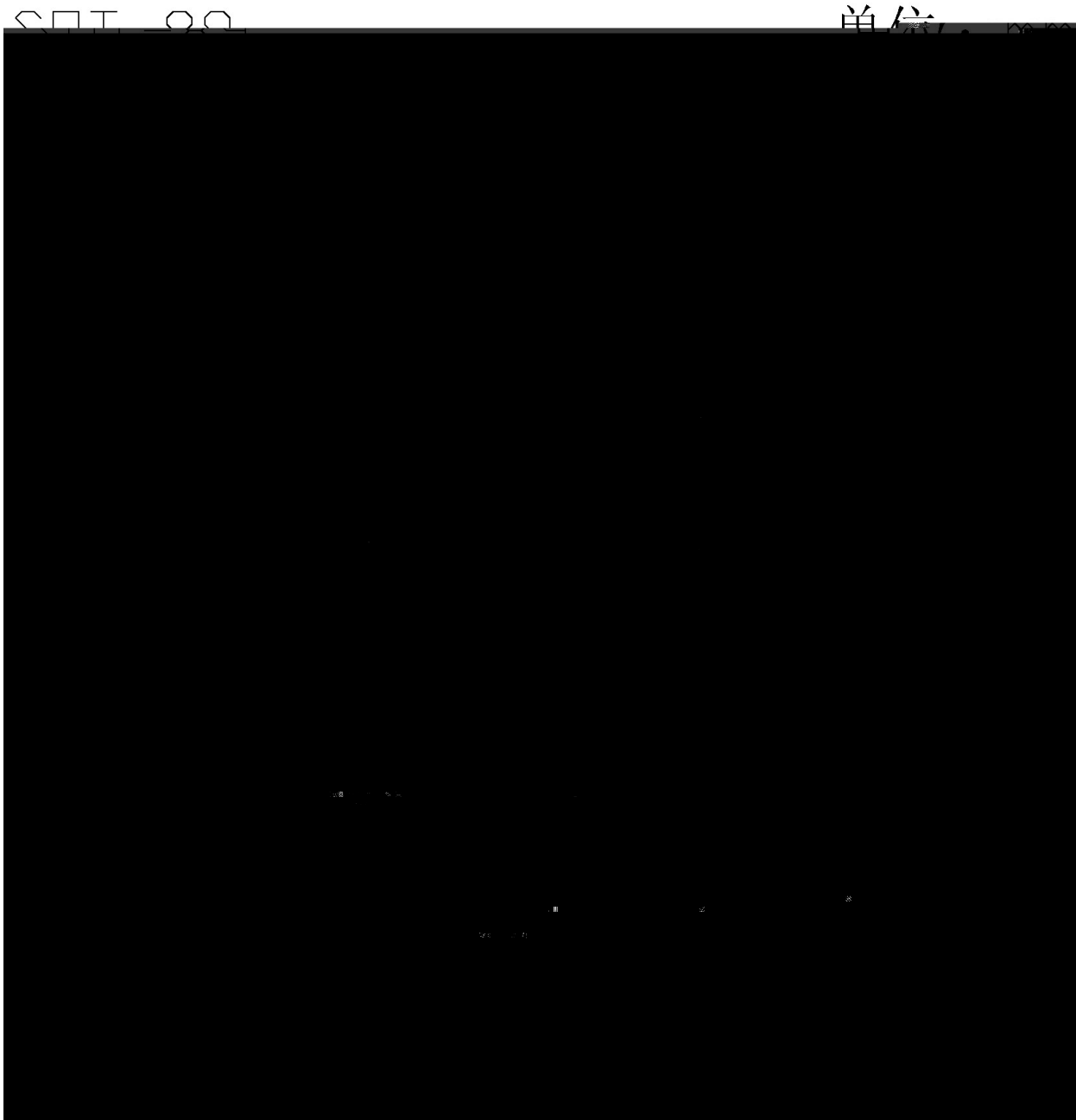
**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=10\mu A$ $I_E=0$	60			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0mA$ $I_B=0$	50			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=10\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=40V$ $I_E=0$			1.0	$\mu A$
Emitter Base Cut-Off Current	$I_{EBO}$	$V_{EB}=4.0V$ $I_C=0$			1.0	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=100mA$	100		400	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=3.0A$	35			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A$ $I_B=100mA$		0.19	0.5	V
Base to Emitter Voltage	$V_{BE}$	$I_C=2.0A$ $I_B=100mA$		0.94	1.2	V
Transition Frequency	$f_T$	$V_{CE}=10V$ $I_C=50mA$		150		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V$ $I_E=0$ $f=1MHz$		25		pF
Turn-On Time	$t_{on}$	$10I_{B1}=-10I_{B2}=I_C=1.0A$		70		nS
Storage Time	$t_{stg}$			650		nS
Fall Time	$t_f$			35		nS

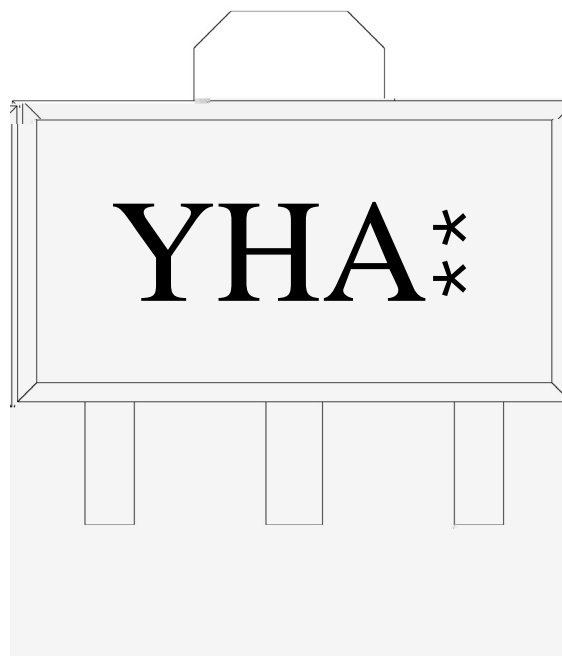
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



Y

H

A

$h_{FE}$

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Note:

Y: Product Type.

H: Company Code.

A  $h_{FE}$  Classifications Symbol

\*\*: Lot No. Code, code change with Lot No.

